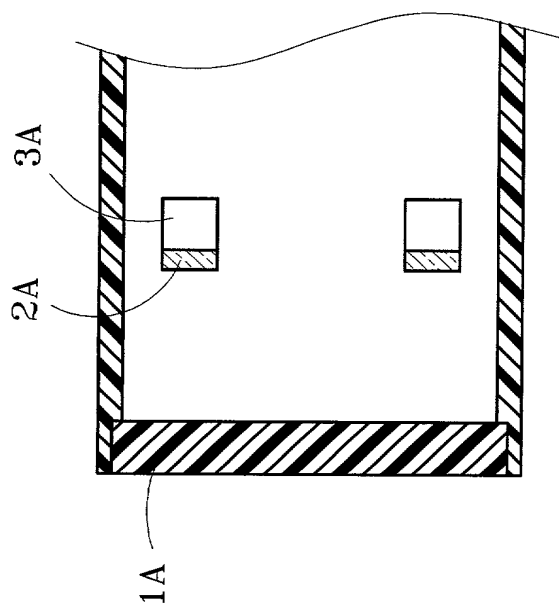
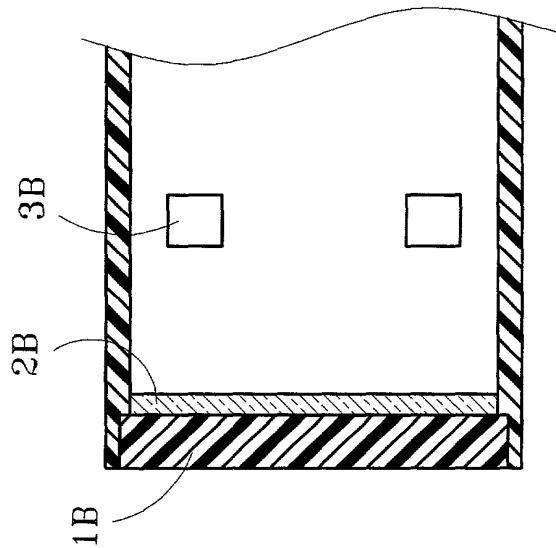


FIG. 1 is a schematic diagram of a prior art device. The device includes a container 1A, a first component 2A, and a second component 3A. The container 1A is shown in cross-section with a hatched pattern. The first component 2A is a rectangular block with a hatched pattern, positioned inside the container 1A. The second component 3A is a rectangular block with a hatched pattern, positioned inside the container 1A. The container 1A is shown with a wavy line indicating a liquid level or a flexible boundary.



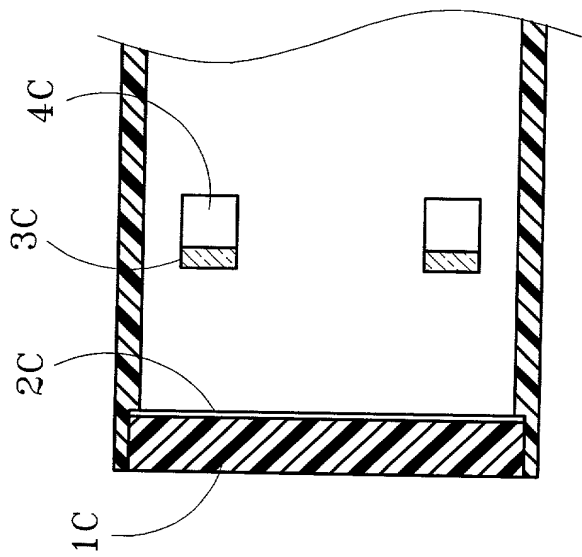
PRIOR ART      Fig. 1

FIG. 2 is a cross-sectional view of a prior art device. The device includes a substrate 1B, a first layer 2B, and a second layer 3B. The first layer 2B is disposed on the substrate 1B, and the second layer 3B is disposed on the first layer 2B. The second layer 3B includes two openings 3A. The first layer 2B includes two openings 2A, each of which is aligned with one of the openings 3A in the second layer 3B. The openings 2A and 3A are in communication with each other.



PRIOR ART      Fig. 2

FIG. 3 is a cross-sectional view of a prior art device. The device includes a substrate 100, a gate dielectric layer 110, a gate electrode 120, a channel layer 130, a source/drain region 140, and a contact layer 150. The contact layer 150 is formed on the source/drain region 140 and is electrically connected to the gate electrode 120. The contact layer 150 is formed of a material having a low work function, such as a metal or a metal silicide. The contact layer 150 is formed on the source/drain region 140 and is electrically connected to the gate electrode 120. The contact layer 150 is formed of a material having a low work function, such as a metal or a metal silicide.



PRIOR ART      Fig. 3

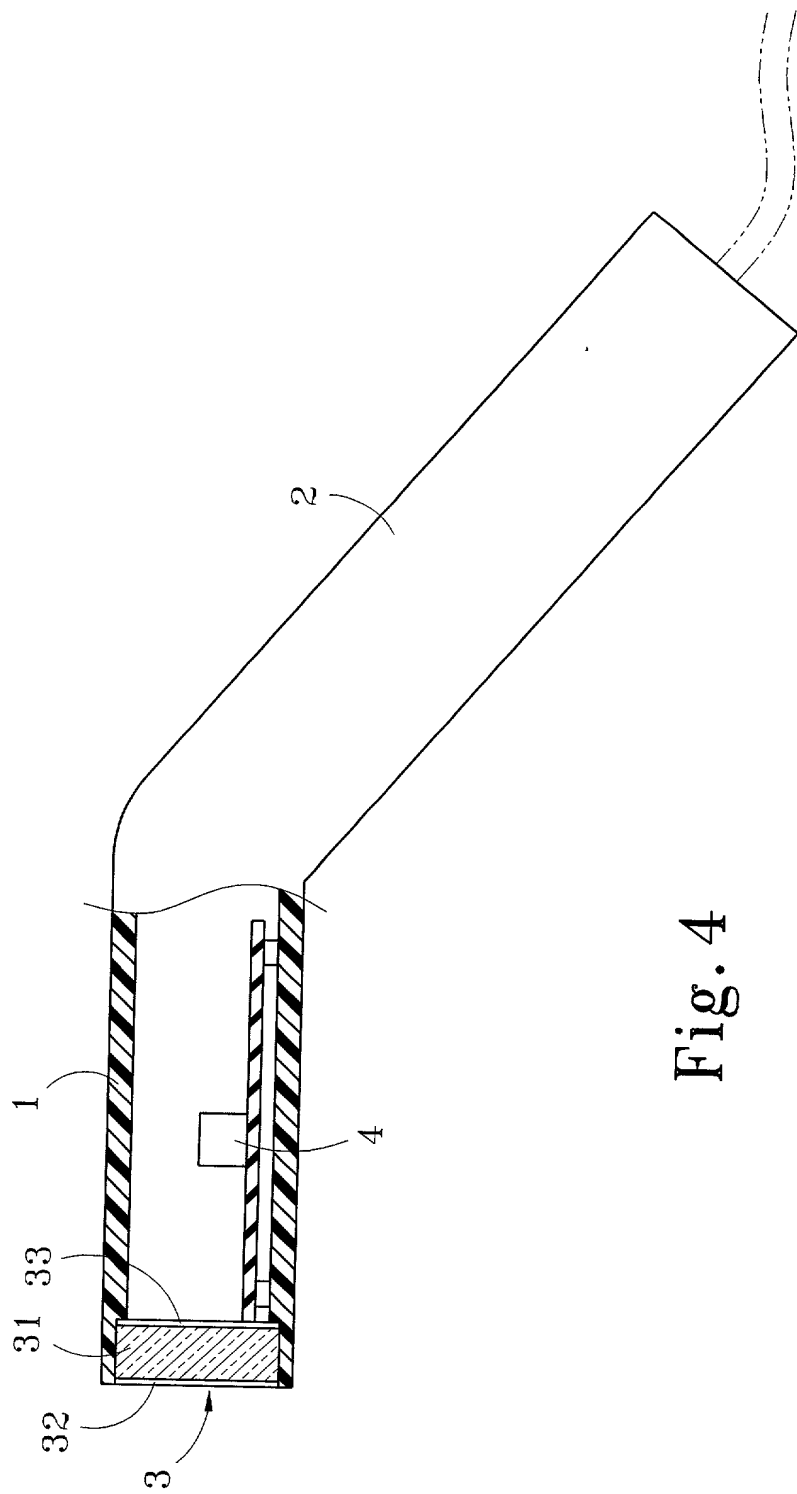


Fig. 4

